March 2015

FDD8782/FDU8782
N-Channel PowerTrench® MOSFET
25V, 35A, 11mΩ

General Description

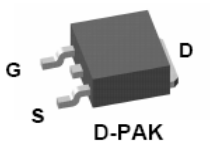
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$ and fast switching speed.

Application

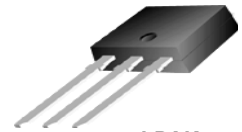
- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture

Features

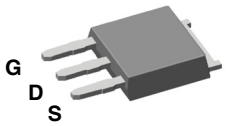
- Max $r_{DS(on)}$ = 11.0mΩ at V_{GS} = 10V, I_D = 35A
- Max $r_{DS(on)}$ = 14.0mΩ at V_{GS} = 4.5V, I_D = 35A
- Low gate charge: $Q_{g(10)}$ = 18nC(Typ), V_{GS} = 10V
- Low gate resistance
- Avalanche rated and 100% tested
- RoHS Compliant



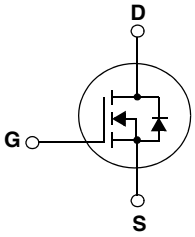
D-PAK
(TO-252)



I-PAK
(TO-251AA)



Short Lead I-PAK



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		25	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	Drain Current -Continuous (Package Limited)		35	A
	-Continuous (Die Limited)		54	
	-Pulsed	(Note 1)	321	
E_{AS}	Single Pulse Avalanche Energy	(Note 2)	72	mJ
P_D	Power Dissipation		50	W
T_J, T_{STG}	Operating and Storage Temperature		-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case TO-252,TO-251	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252,TO-251	100	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252,1in^2 copper pad area	52	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8782	FDD8782	TO-252AA	13”	16mm	2500 units
FDU8782	FDU8782	TO-251AA	N/A(Tube)	N/A	75 units
FDU8782	FDU8782_F071	TO-251AA	N/A(Tube)	N/A	75 units

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Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	25			V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		14.3		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20V, V_{GS} = 0V			1	μA
		T_J = 150°C			250	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.2	1.7	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-6.5		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10V, I_D = 35A		8.5	11.0	mΩ
		V_{GS} = 4.5V, I_D = 35A		11.0	14.0	
		V_{GS} = 10V, I_D = 35A, T_J = 175°C		12.1	18.0	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 13V, V_{GS} = 0V, f = 1MHz		920	1220	pF
C_{oss}	Output Capacitance			230	310	pF
C_{rss}	Reverse Transfer Capacitance			160	240	pF
R_g	Gate Resistance	f = 1MHz		1.4		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 13V, I_D = 35A, V_{GS} = 10V, R_{GS} = 9Ω		7	14	ns
t_r	Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			22	36	ns
t_f	Fall Time			14	25	ns
Q_g	Total Gate Charge	V_{GS} = 0V to 10V, V_{DD} = 13V, I_D = 35A, I_g = 1.0mA		18	25	nC
Q_g	Total Gate Charge	V_{GS} = 0V to 5V, V_{DD} = 13V, I_D = 35A, I_g = 1.0mA		9.4	13	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 13V, I_D = 35A, I_g = 1.0mA		3.1		nC
Q_{gd}	Gate to Drain “Miller”Charge	V_{DD} = 13V, I_D = 35A, I_g = 1.0mA		4.0		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 35A		0.96	1.25	V
		V_{GS} = 0V, I_S = 15A		0.86	1.2	
t_{rr}	Reverse Recovery Time	I_F = 35A, di/dt = 100A/μs		25	38	ns
Q_{rr}	Reverse Recovery Charge	I_F = 35A, di/dt = 100A/μs		17	26	nC

Notes:
1: Pulse time < 300us,Duty cycle = 2%.
2: Starting T_J = 25°C, L = 1.0mH, I_{AS} = 12A ,V_{DD} = 23V, V_{GS} = 10V.

Typical Characteristics T_J = 25°C unless otherwise noted

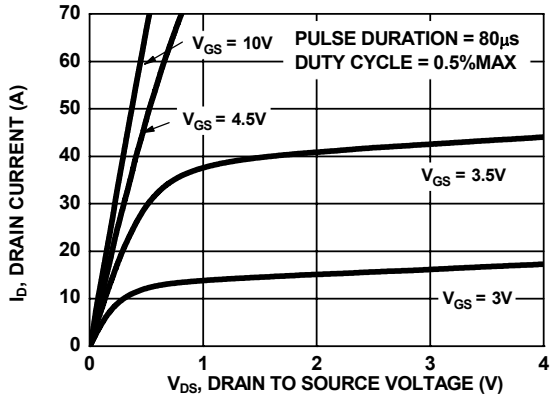


Figure 1. On Region Characteristics

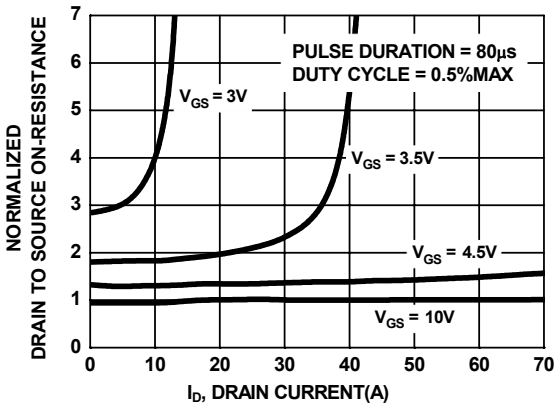


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

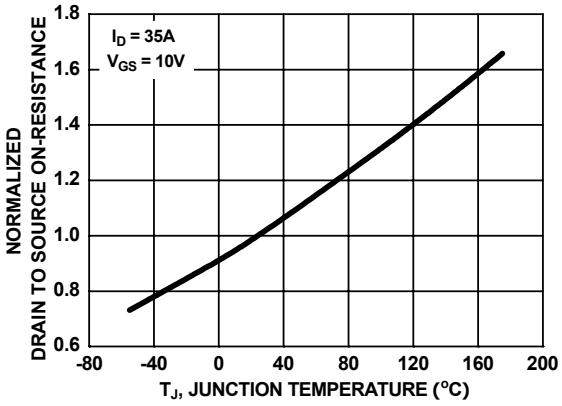


Figure 3. Normalized On Resistance vs Junction Temperature

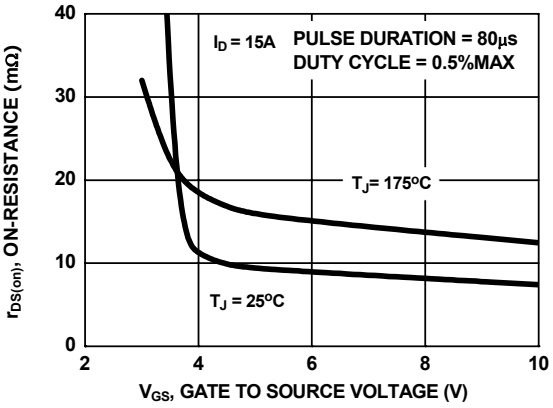


Figure 4. On-Resistance vs Gate to Source Voltage

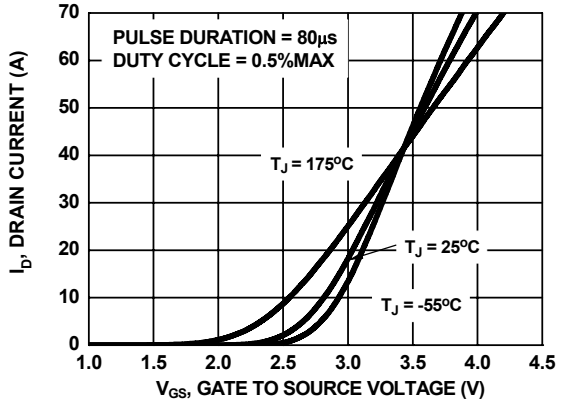


Figure 5. Transfer Characteristics

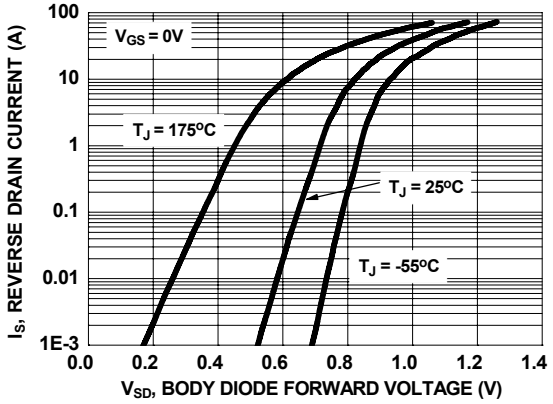


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

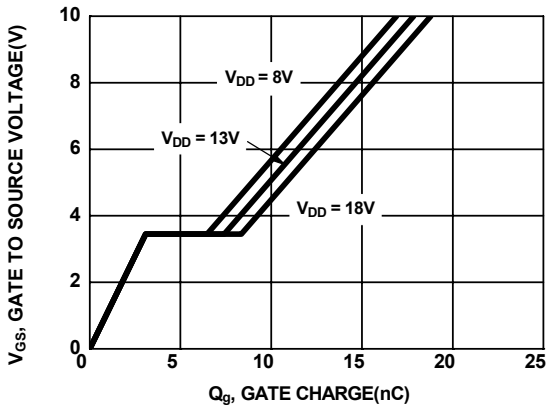


Figure 7. Gate Charge Characteristics

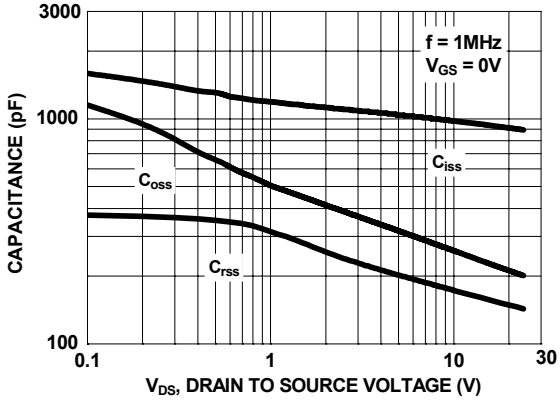


Figure 8. Capacitance vs Drain to Source Voltage

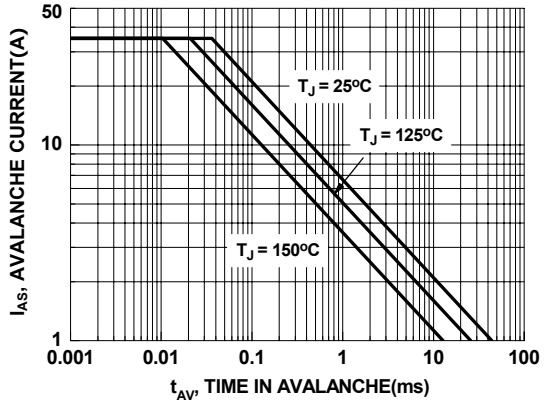


Figure 9. Unclamped Inductive Switching Capability

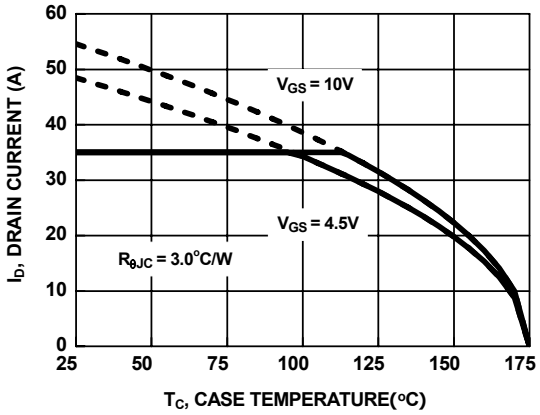


Figure 10. Maximum Continuous Drain Current vs Case Temperature

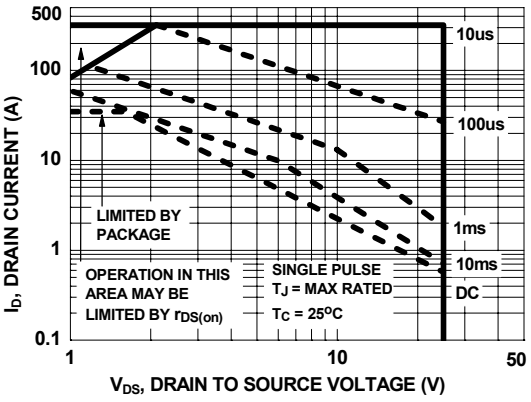


Figure 11. Forward Bias Safe Operating Area

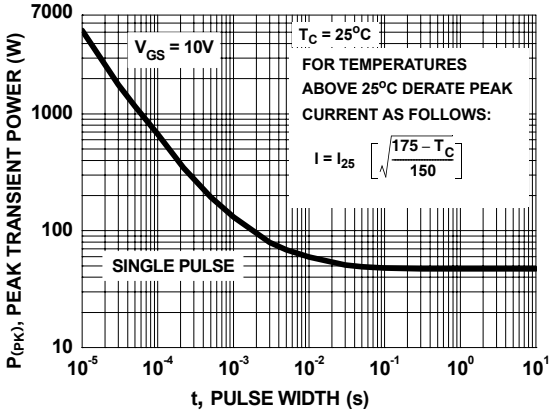


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

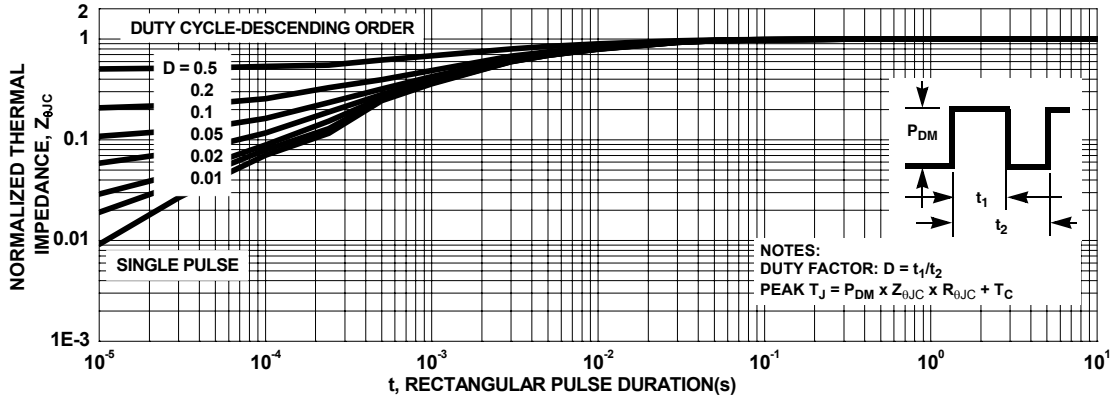
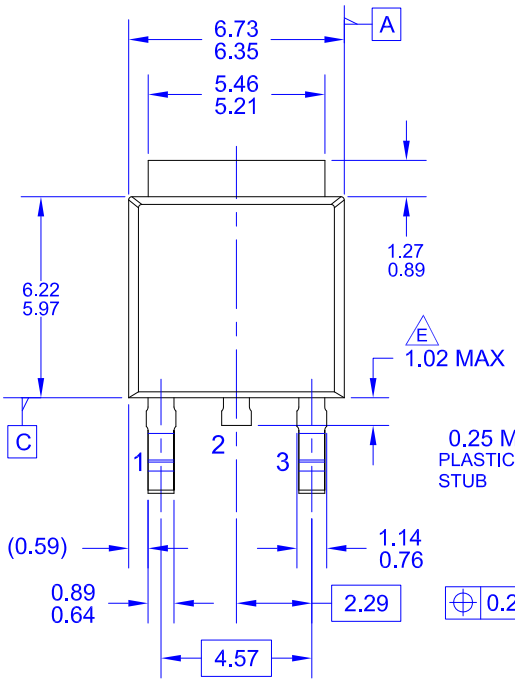
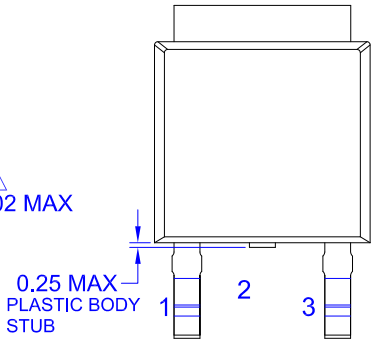


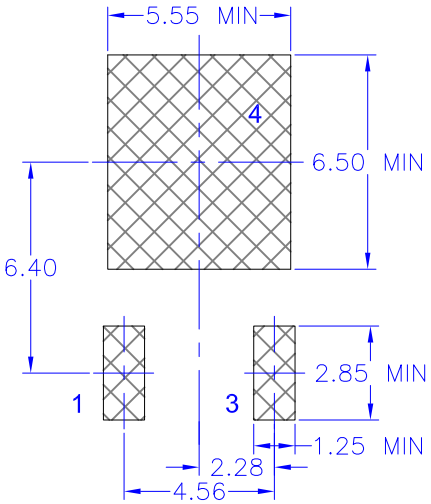
Figure 13. Transient Thermal Response Curve



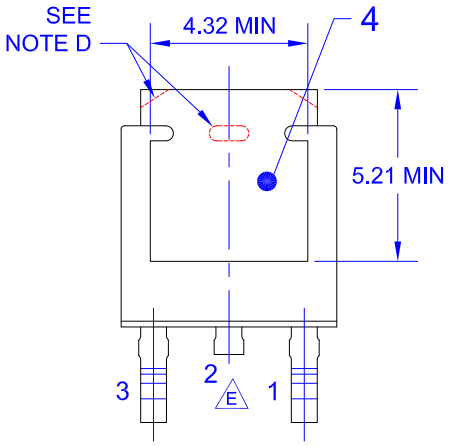
NON-DIODE PRODUCTS VERSION



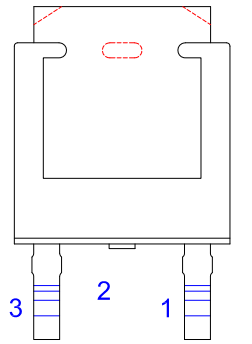
DIODE PRODUCTS VERSION



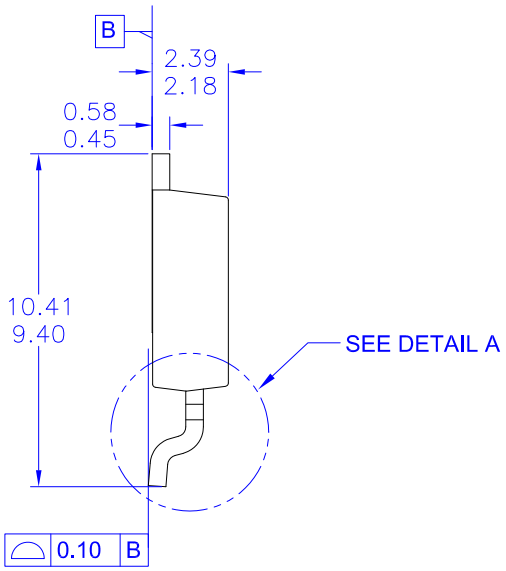
LAND PATTERN RECOMMENDATION



NON-DIODE PRODUCTS VERSION

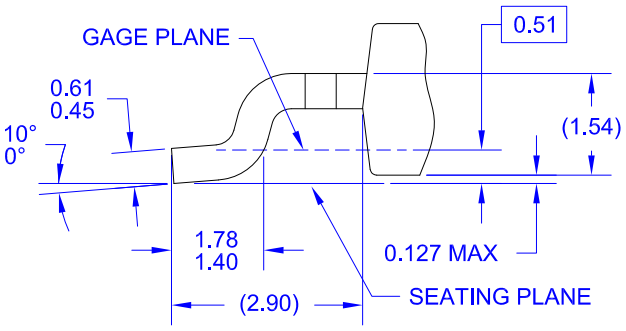


DIODE PRODUCTS VERSION



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV10



DETAIL A
(ROTATED -90°)
SCALE: 12X

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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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